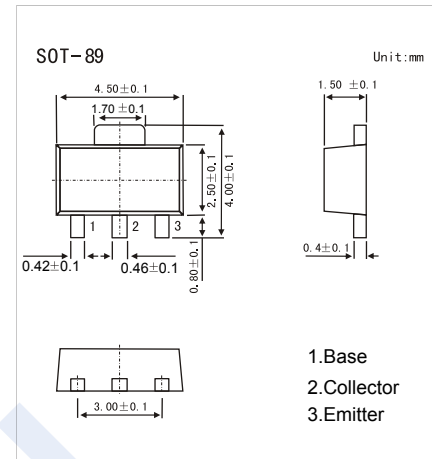


PNP Transistors

2SB1308

■ Features

- Power Transistor
- Excellent DC current Gain
- Low Collector-emitter Saturation Voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-30	V
Collector - Emitter Voltage	V _{CEO}	-20	
Emitter - Base Voltage	V _{EBO}	-6	
Collector Current - Continuous	I _c	-3	A
Collector Power Dissipation	P _c	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-30			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-20			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _c =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -25V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _c =0			-0.5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-1.5 A, I _B =-150 mA			-0.45	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-1.5 A, I _B =-150 mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -2V, I _c = -500 mA	82		390	
Collector output capacitance	C _{ob}	V _{CB} = -20V, I _E = 0, f=1MHz		60		pF
Transition frequency	f _t	V _{CE} = -6V, I _c = -50 mA, f=30MHz		120		MHz

■ Classification of h_{FE}

Type	2SB1308-P	2SB1308-Q	2SB1308-R
Range	82-180	120-270	180-390
Marking	BF P*	BF Q*	BF R*

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2SB1308

Typical Characteristics

